

BTA2008 series D and E

0.8 A Three-quadrant triacs high commutation

Rev. 01 — 18 January 2008

Product data sheet

1. Product profile

1.1 General description

Passivated, guaranteed commutation, sensitive gate triacs in a SOT54 plastic package

1.2 Features

- Guaranteed commutation performance at each gate sensitivity
- Easily interfaced with low power drivers including microcontrollers
- Sensitive gate

1.3 Applications

- Motor control
- Solenoid drivers

1.4 Quick reference data

- $V_{\text{DRM}} \leq 600 \text{ V}$ (BTA2008-600D)
- $V_{\text{DRM}} \leq 600 \text{ V}$ (BTA2008-600E)
- $V_{\text{DRM}} \leq 800 \text{ V}$ (BTA2008-800D)
- $V_{\text{DRM}} \leq 800 \text{ V}$ (BTA2008-800E)
- $I_{\text{TSM}} \leq 9 \text{ A}$ ($t = 20 \text{ ms}$)
- $I_{\text{GT}} \leq 5 \text{ mA}$ (BTA2008-600D)
- $I_{\text{GT}} \leq 5 \text{ mA}$ (BTA2008-800D)
- $I_{\text{GT}} \leq 10 \text{ mA}$ (BTA2008-600E)
- $I_{\text{GT}} \leq 10 \text{ mA}$ (BTA2008-800E)
- $I_{\text{T(RMS)}} \leq 0.8 \text{ A}$

2. Pinning information

Table 1. Pinning

Pin	Description	Simplified outline	Graphic symbol
1	main terminal 2 (T2)	<p>SOT54 (TO-92)</p>	<p>T2—T1 G sym051</p>
2	gate (G)		
3	main terminal 1 (T1)		

3. Ordering information

Table 2. Ordering information

Type number	Package		Version
	Name	Description	
BTA2008-600D	TO-92	plastic single-ended leaded (through hole) package; 3 leads	SOT54
BTA2008-600E			
BTA2008-800D			
BTA2008-800E			

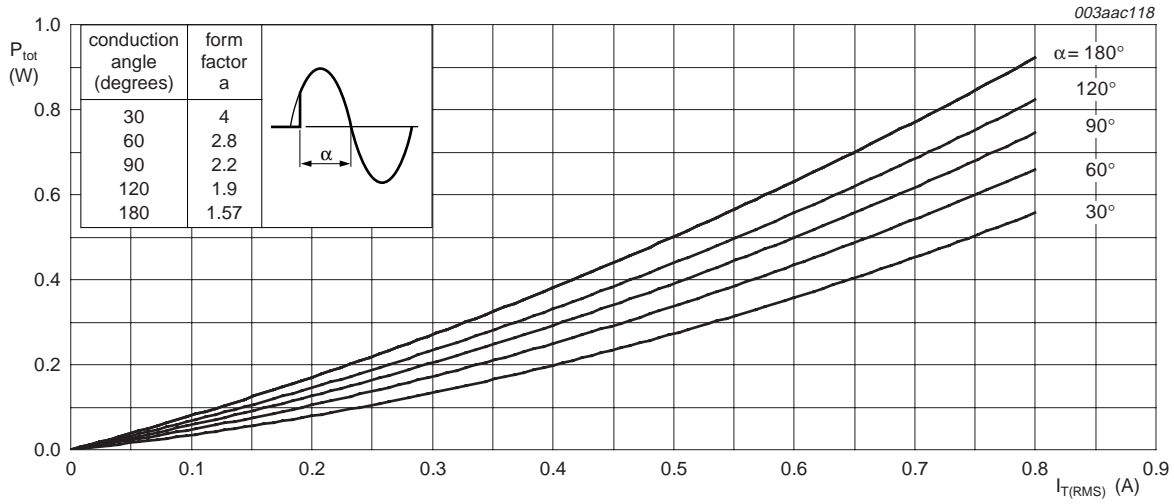
4. Limiting values

Table 3. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

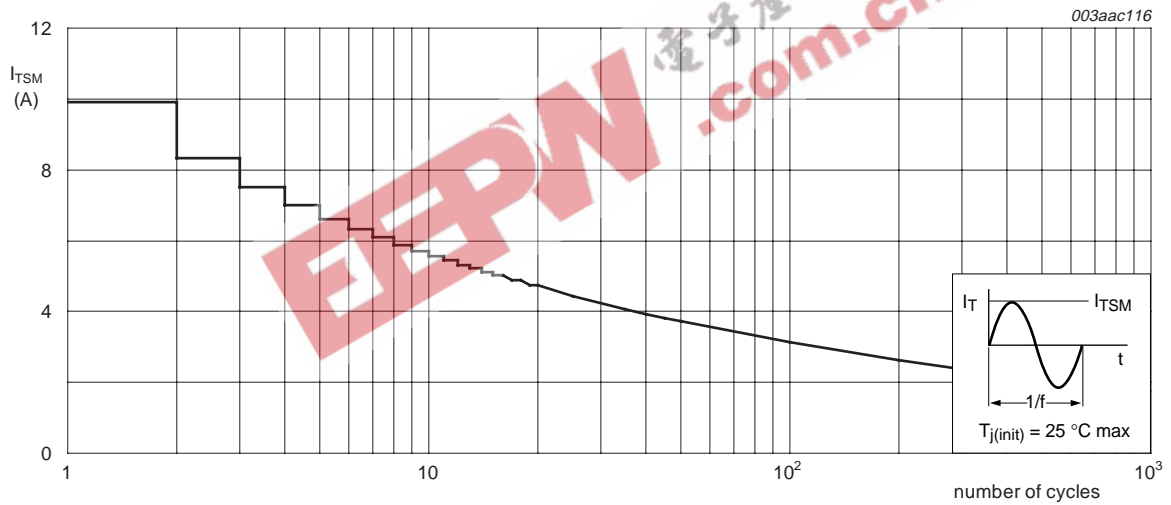
Symbol	Parameter	Conditions	Min	Max	Unit
V_{DRM}	repetitive peak off-state voltage	BTA2008-600D; BTA2008-600E ^[1]	-	600	V
		BTA2008-800D; BTA2008-800E	-	800	V
$I_{\text{T(RMS)}}$	RMS on-state current	full sine wave; $T_{\text{lead}} \leq 70\text{ °C}$; see Figure 4 and 5	-	0.8	A
I_{TSM}	non-repetitive peak on-state current	full sine wave; $T_{\text{j}} = 25\text{ °C}$ prior to surge; see Figure 2 and 3	-	-	-
		$t = 20\text{ ms}$	-	9	A
		$t = 16.7\text{ ms}$	-	9.9	A
I^2t	I^2t for fusing	$t_{\text{p}} = 10\text{ ms}$	-	0.41	A ² s
di_{T}/dt	rate of rise of on-state current	$I_{\text{TM}} = 1.5\text{ A}$; $I_{\text{G}} = 20\text{ mA}$; $di_{\text{G}}/dt = 0.2\text{ A}/\mu\text{s}$	-	100	A/ μs
I_{GM}	peak gate current		-	1	A
P_{GM}	peak gate power		-	5	W
$P_{\text{G(AV)}}$	average gate power	over any 20 ms period	-	0.1	W
T_{stg}	storage temperature		-40	+150	°C
T_{j}	junction temperature		-	125	°C

- [1] Although not recommended, off-state voltages up to 800 V may be applied without damage, but the triac may switch to the on-state. The rate of rise of current should not exceed 6 A/ μs .



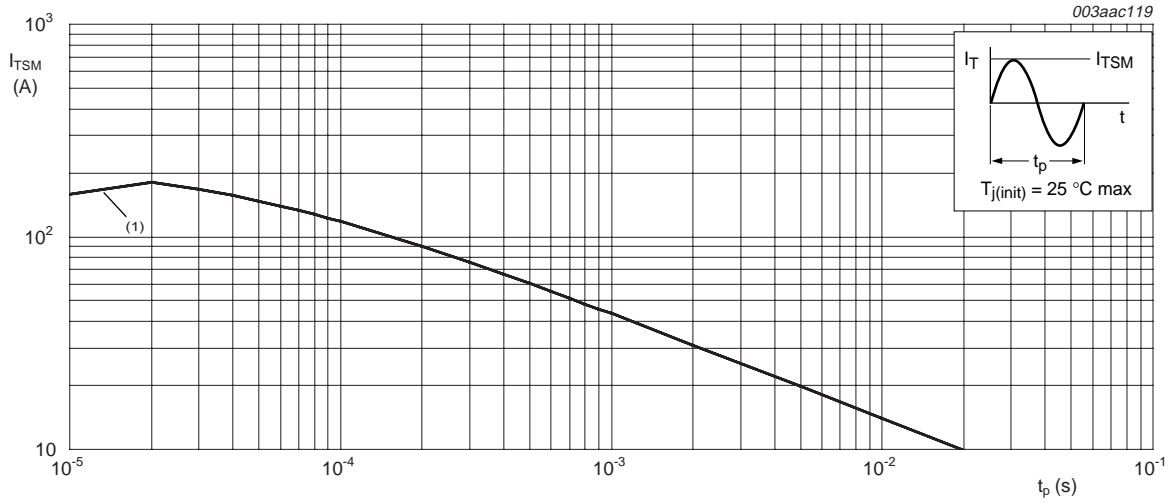
α = conduction angle

Fig. 1. Total power dissipation as a function of RMS on-state current; maximum values



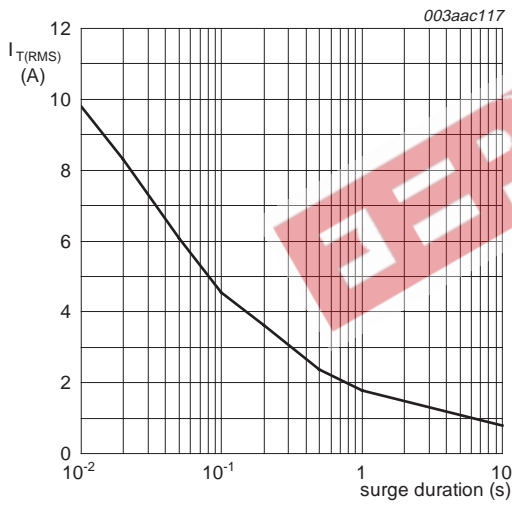
$f = 50$ Hz

Fig. 2. Non-repetitive peak on-state current as a function of the number of sinusoidal current cycles; maximum values



$t_p \leq 20 \text{ ms}$
 (1) di_T/dt limit

Fig 3. Non-repetitive peak on-state current as a function of pulse duration; maximum values



$f = 50 \text{ Hz}$
 $T_{\text{lead}} = 70 \text{ }^\circ\text{C}$

Fig 4. RMS on-state current as a function of surge duration; maximum values

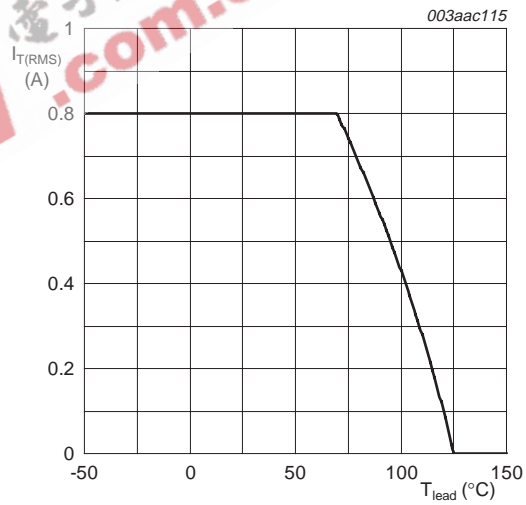


Fig 5. RMS on-state current as a function of lead temperature; maximum values

5. Thermal characteristics

Table 4. Thermal characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$R_{th(j-lead)}$	thermal resistance from junction to lead	full cycle; see Figure 6	-	-	60	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient	printed circuit board mounted; lead length 4 mm	-	150	-	K/W

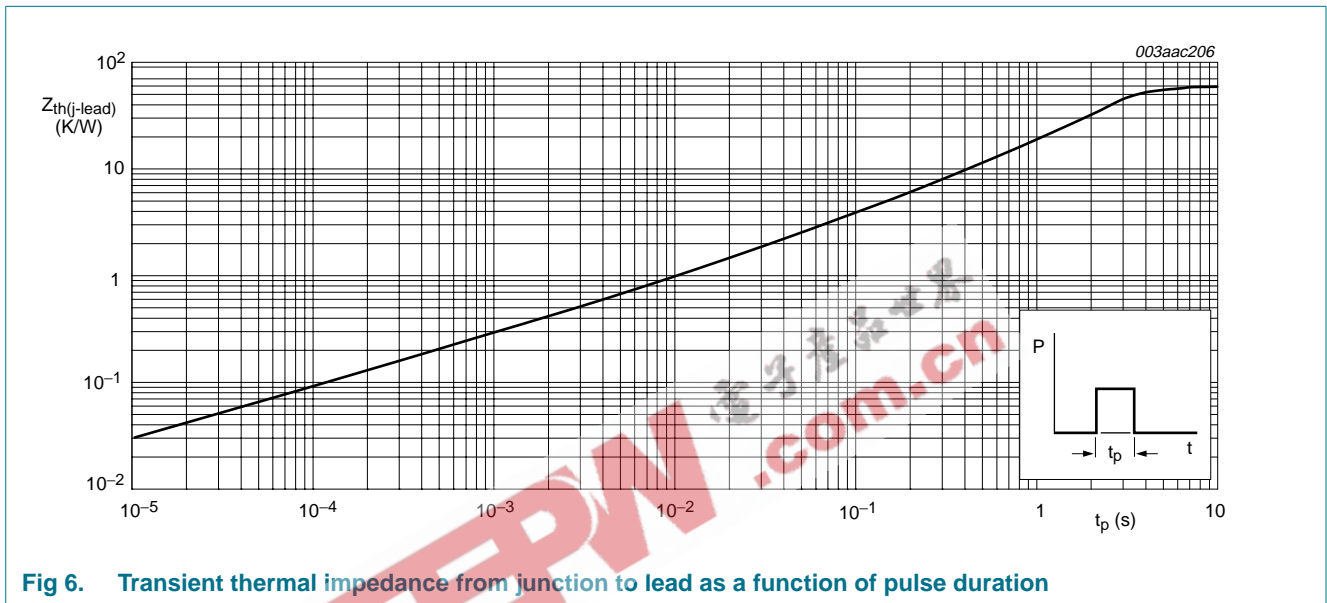


Fig 6. Transient thermal impedance from junction to lead as a function of pulse duration

6. Static characteristics

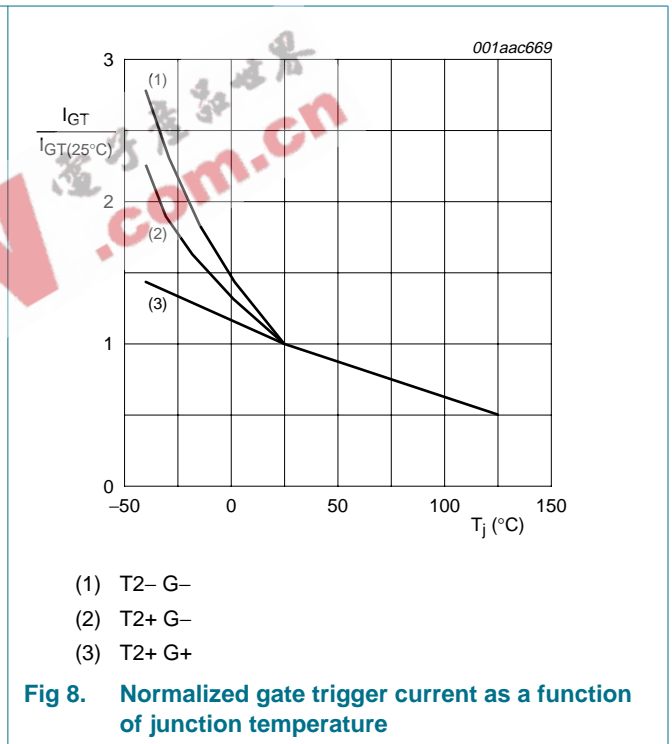
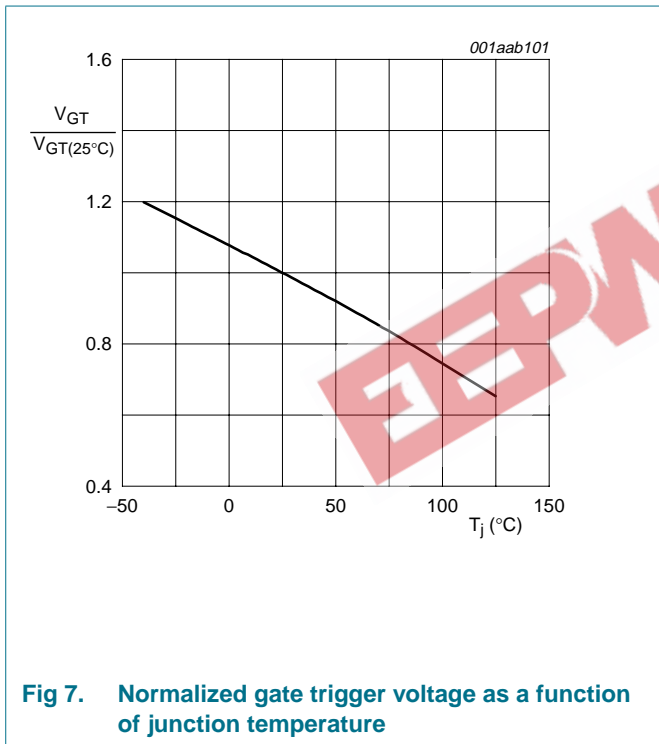
Table 5. Static characteristics
T_j = 25 °C unless otherwise specified.

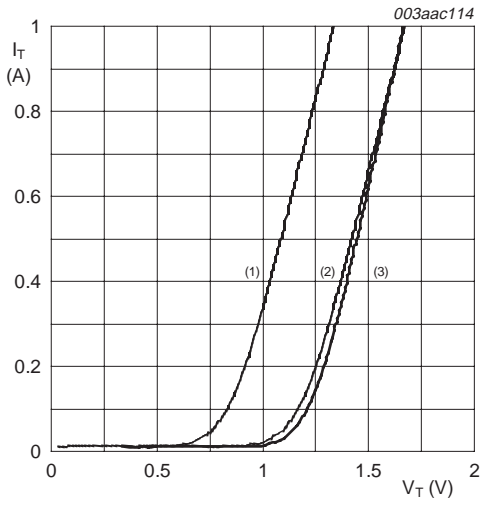
Symbol	Parameter	Conditions	BTA2008-600D BTA2008-800D			BTA2008-600E BTA2008-800E			Unit
			Min	Typ	Max	Min	Typ	Max	
I _{GT}	gate trigger current	V _D = 12 V; I _T = 0.1 A; see Figure 8							
		T2+ G+	0.25	-	5	0.5	-	10	mA
		T2+ G-	0.25	-	5	0.5	-	10	mA
I _L	latching current	V _D = 12 V; I _{GT} = 0.1 A; see Figure 10							
		T2+ G+	-	-	10	-	-	12	mA
		T2+ G-	-	-	20	-	-	20	mA
I _H	holding current	V _D = 12 V; I _{GT} = 0.1 A; see Figure 11							
		T2- G-	-	-	10	-	-	12	mA
		T2- G-	-	-	10	-	-	12	mA
V _T	on-state voltage	I _T = 0.85 A; see Figure 9		1.35	1.6	-	1.35	1.6	V
V _{GT}	gate trigger voltage	V _D = 12 V; I _T = 0.1 A; see Figure 7		0.9	2	-	0.9	2	V
		V _D = 400 V; I _T = 0.1 A; T _j = 125 °C	0.2	0.3	-	0.2	0.3	-	V
I _D	off-state current	V _D = V _{DRM(max)} ; T _j = 125 °C	-	0.1	0.5	-	0.1	0.5	mA

7. Dynamic characteristics

Table 6. Dynamic characteristics

Symbol	Parameter	Conditions	BTA2008-600D BTA2008-800D			BTA2008-600E BTA2008-800E			Unit
			Min	Typ	Max	Min	Typ	Max	
			dV_D/dt	rate of rise of off-state voltage	$V_{DM} = 0.67 \times V_{DRM(max)}$; $T_j = 125\text{ }^\circ\text{C}$; exponential waveform; gate open circuit	200	-	-	
di_{com}/dt	rate of change of commutating current	$V_{DM} = 400\text{ V}$; $T_j = 125\text{ }^\circ\text{C}$; $I_{T(RMS)} = 0.8\text{ A}$; $dV/dt = 10\text{ V}/\mu\text{s}$; gate open circuit	0.5	-	-	1.6	-	-	A/ms
t_{gt}	gate-controlled turn-on time	$I_{TM} = 1\text{ A}$; $V_D = V_{DRM(max)}$; $I_G = 0.1\text{ A}$; $di_G/dt = 5\text{ A}/\mu\text{s}$	-	2	-	-	2	-	μs





- $V_o = 0.835 \text{ V}$
 $R_s = 0.5 \text{ } \Omega$
- (1) $T_j = 125 \text{ } ^\circ\text{C}$; typical values
 - (2) $T_j = 125 \text{ } ^\circ\text{C}$; maximum values
 - (3) $T_j = 25 \text{ } ^\circ\text{C}$; maximum values

Fig 9. On-state current as a function of on-state voltage

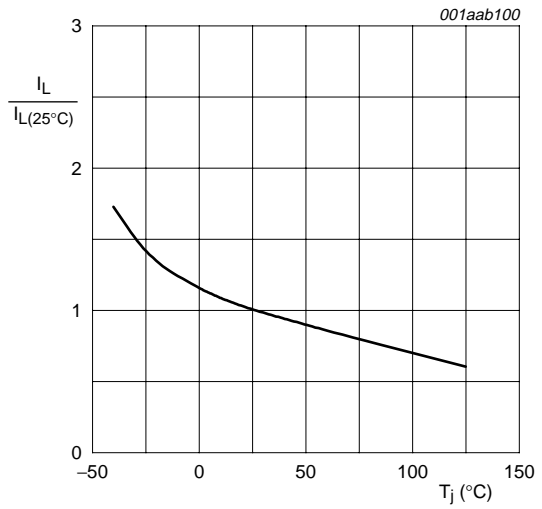


Fig 10. Normalized latching current as a function of junction temperature

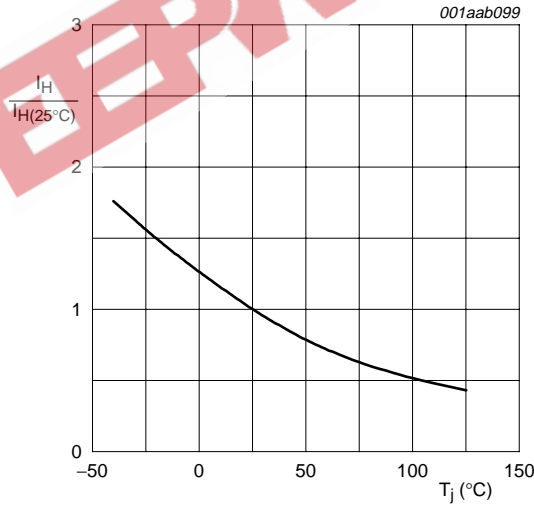


Fig 11. Normalized holding current as a function of junction temperature

8. Package outline

Plastic single-ended leaded (through hole) package; 3 leads

SOT54

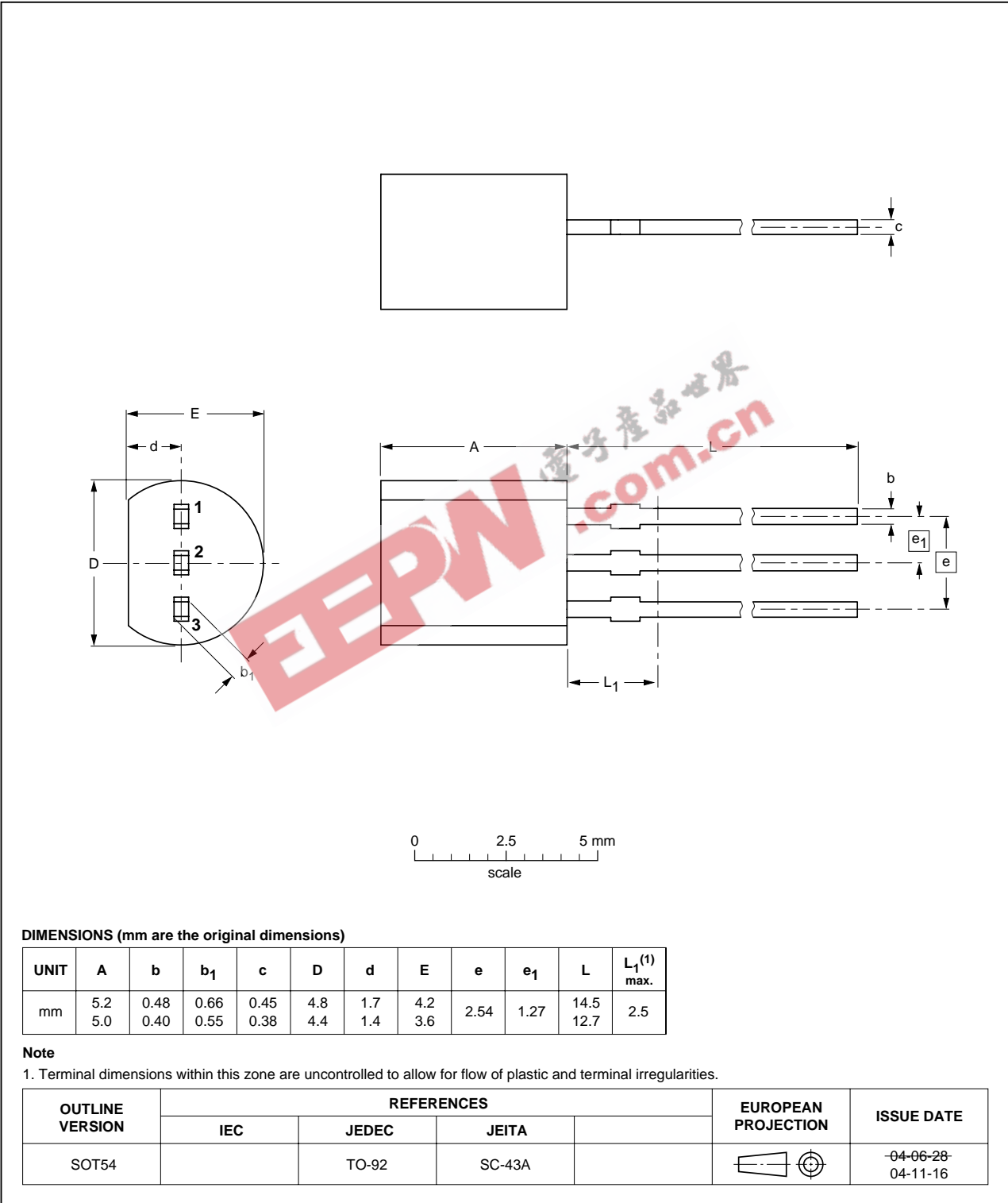


Fig 12. Package outline SOT54 (TO-92)

9. Revision history

Table 7. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
BTA2008_SER_D_E_1	20080118	Product data sheet	-	-

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10.1 Data sheet status

Document status ^{[1][2]}	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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12. Contents

1 Product profile 1

1.1 General description 1

1.2 Features 1

1.3 Applications 1

1.4 Quick reference data 1

2 Pinning information 1

3 Ordering information 2

4 Limiting values 2

5 Thermal characteristics 5

6 Static characteristics 6

7 Dynamic characteristics 7

8 Package outline 9

9 Revision history 10

10 Legal information 11

10.1 Data sheet status 11

10.2 Definitions 11

10.3 Disclaimers 11

10.4 Trademarks 11

11 Contact information 11

12 Contents 12



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